

	L #	Hits	Search Text	DBs	Time Stamp
1	L168	34053	((etch\$3 remov\$3)) near5 ((oxide dioxide oxidized oxidised) near5 (silicon polysilicon (poly adj silicon)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 17:49
2	L175	2756	168 same (clean\$3 contaminant contamination)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 17:51
3	L182	196	175 same silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 17:53
4	L189	189	182 and ((layer film wire wiring gate) near5 (silicon polysilicon (poly adj silicon)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 17:52
5	L196	5703	168 same ((oxidiz\$3 oxidis\$3 oxidation) near5 (silicon polysilicon (poly adj silicon)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 17:51
6	L203	356	196 same (clean\$3 contaminant contamination)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 17:51
7	L210	340	203 and ((layer film wire wiring gate) near5 (silicon polysilicon (poly adj silicon)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 17:52
8	L217	86	203 and silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 17:53

	L #	Hits	Search Text	DBs	Time Stamp
1	L1	612	carbon near10 silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 13:53
2	L8	44	(carbon near3 (contaminat\$3 mixture mix\$3)) near10 silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 13:57
3	L15	1966	(carbon near3 (contaminat\$3 mixture mix\$3)) near10 (silicon polysilicon (poly adj silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 14:08
4	L22	23	15 same silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 14:14
5	L29	583	(carbon near3 (remov\$3)) near10 (silicon polysilicon (poly adj silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 14:09
6	L36	36	29 and silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 14:14